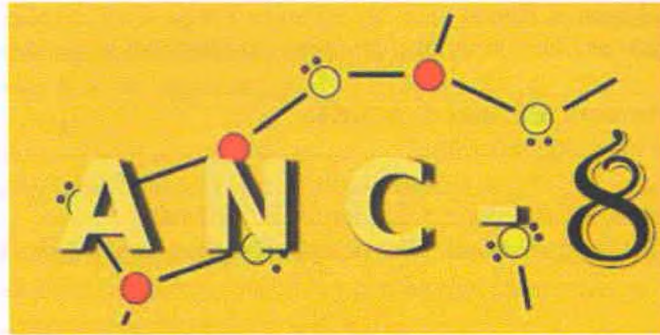


# Abstract Book

**8<sup>th</sup> International Conference on  
Amorphous and Nanostructured Chalcogenides**

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## Contents

### ***Invited Papers***

P. Boolchand <i>Correlating melt dynamics with glass topological phases in chalcogenides</i> .....	1
L. Calvez <i>Ga-based chalcogenide glass-ceramics transparent in the infrared</i> .....	1
E. A. Chechetkina <i>Bond waves in thin films: Photostructural changes and electrical switching in amorphous chalcogenides</i> .....	2
S. Hosokawa, J. R. Stellhorn <i>Local structural analysis for chalcogenide functional materials</i> .....	2
G. Kaur Ahluwalia <i>Applications of Chalcogenides S, Se and Te</i> .....	3
S. Kökényesi <i>Plasmon assisted optical recording in amorphous nanocomposites</i> .....	4
A. Kovalskiy, R. Golovchak, M. White, J. Allen, L. Nicholls, K. Palka, M. Vlcek, H. Jain <i>In situ kinetics of photoinduced effects in thermally deposited and spin-coated chalcogenide glass thin films</i> .....	5
A. A. Kryuchyn, V. V. Petrov, V. M. Rubish, M. L. Trunov, S. A. Kostyukevich <i>Formation of nanoscale structures on chalcogenide films</i> .....	5
S. Kugler <i>Photoinduced bond breaking and volume change in chalcogenide glasses</i> .....	6
V. S. Minaev <i>Polymorphism and intermediate-range order – the basis of the structure of glassy and non-glassy of non-crystalline individual chemical substances</i> .....	6
N. Mousseau <i>Understanding the long-time kinetics of disordered and complex materials with the kinetic activation-relaxation technique</i> .....	7
T. Nichol, M. R. Latif, M. Ailavjhala, M. Mitkova <i>Interaction of Ge-Se films with ions: Structural studies and application for memory arrays formation</i> .....	7

A. Piarristeguy, A. Pradel, P. Jóvári, I. Kaban <i>Te-based chalcogenide amorphous films: structural and physico-chemical properties</i> .....	8
M. Popescu, F. Sava, I.D. Simandan, A. Lőrinczi, A. Velea <i>Freestanding thin amorphous chalcogenide films</i> .....	9
J. Rocca, V. Bilovol, M. Fontana, M. A. Ureña, J. L. García, B. Arcondo <i>Chalcogenide glasses for PCRAM applications. Characterization from large to short range order</i> .....	9
J. Singh <i>Excitons to photocarrier generations in bulk heterojunction organic solar cells</i> .....	10
J. Teteris <i>Photoinduced mass transport in amorphous chalcogenide and azobenzene organic materials</i> .....	10
D. Tsiulyanu <i>Remarks on surface and transport phenomena in chalcogenide glassy semiconductors</i> .....	11
A. Velea, K. Opsomer, W. Devulder, J. Dumortier, J. Fan, C. Detavernier, M. Jurczak, B. Govoreanu <i>Chalcogenide materials for selectors and phase change memories</i> .....	12
M. Wuttig <i>Novel phase change materials by design: the mystery of resonance bonding</i> .....	13

### **Regular Papers – Oral Session**

P. E. Agbo, P. A. Nwofe, L. O. Odo <i>Effect of dye addition on the structural and optical properties of AlZnS thin films</i> .....	14
R. I. Alekberov, M. Fabián, A. I. Isayev, S. I. Mekhtiyeva <i>The local structure and optical properties of <math>As_{40}Se_{60}</math>, <math>As_{40}Se_{30}S_{30}</math>, <math>As_{40}Se_{30}Te_{30}</math> chalcogenide glasses</i> .....	14
D. K. Dwivedi <i>Selenium based semiconducting non-oxide glasses for optical data storage</i> .....	15
S. Dyussebaev, O. Prikhodko, A. Sazonov, Z. Tolepov, N. Almasov, S. Maksimova, N. Guseinov, S. Kozyukhin <i>Electronic properties of nanosized <math>Ge_2Sb_2Te_5&lt;Bi&gt;</math> films</i> .....	16
S. Kozyukhin, Yu. Vorobyov, P. Lazarenko, M. Presniakov, A. Pevtsov <i>Isothermal and laser crystallization of amorphous <math>Ge_2Sb_2Te_5</math> thin films</i> .....	17
M. Kristl, S. Gyergyek, J. Kristl <i>Nanostructured nickel sulfides with different stoichiometries prepared by mechanochemical synthesis</i> .....	17
V. Mitsa, A. Feher, S. Petretskij, R. Holomb, V. Tkac <i>Hysteresis of low temperature thermal conductivity, Boson peak in glassy (g) <math>As_2S_3</math> and low frequency ring and branched <math>AsnSm</math> clusters vibrations</i> .....	18
G. Osayemwenre, E. Meyer, T. R. Taziwa <i>Stress analysis in a degraded monocrystalline solar cell by Raman Spectroscopy</i> .....	18

A. Sherchenkov, S. Kozyukhin, A. Babich, P. Lazarenko, V. Kalugin, S. Timoshenkov <i>Crystallization mechanism and kinetic parameters in <math>Ge_2Sb_2Te_5</math> thin films for the phase change memory application</i> .....	19
P. K. Singh, D. K. Dwivedi <i>Effect of thermal annealing on structural and optical properties of <math>Se_{66}Te_{25}In_9</math> thin films</i> .....	19
J. R. Stellhorn, W.-C. Pilgrim, Y. Sutou, S. Hosokawa <i>A combination of anomalous X-ray scattering and X-ray absorption fine structure experiments for the characterization of amorphous <math>GeCu_2Te_3</math></i> .....	20
V. I. Verlan, P. Bardetchi, O. Bordian, M. S. Iovu, I. Culeac, V. E. Zubareva <i>Energy transfer from UV to red in the polymer/nanocomposites with <math>Eu^{3+}</math> coordination compounds</i> .....	21
 <b>Regular Papers - Poster Session</b>	
I. Baník <i>Optical phenomena in chalcogenide glass-fibers illuminated with lateral excited band-gap light</i> .....	22
L. Baschir, C. Opran, D. Savastru, S. Miclos, A. Popescu <i>Spectroscopic ellipsometric study of <math>As_2S_3</math> RF sputtered thin films</i> .....	22
V. Bilanych, V. Komanicky, A. Feher, V. Kuzma, V. Rizak <i>Dynamic Taylor cone formation on chalcogenide films surface</i> .....	23
V. Bilanych, V. Komanicky, M. Kozejova, A. Feher, A. Kovalcikova, F. Lofaj, V. Kuzma, V. Rizak <i>Influence of size factors on the formation of surface relief in amorphous chalcogenide films during periodic charge deposition by electronic beam</i> .....	23
V. Bilanych, K. Flachbart, A. Jurikova, K. Csach, V. Rizak <i>Relaxation processes in chalcogenide glasses</i> .....	24
E. A. Chechetkina <i>Ultrasound modulation of the structure of glassy chalcogenides</i> .....	24
M. Ciobanu <i>DC conductivity in <math>As_2S_3</math> <math>Ge_8Te_x</math> amorphous thin films</i> .....	25
S. Cozic, A. Castro, O. Bošák, M. Kubliha, V. Labaš, L. Calvez, D. Le Coq <i>Synthesis and electrical characterization of Li-based sulfide glasses</i> .....	26
A. Duta, A. Enesca, D. Perniu, M. Covei, L. Isac <i>Low cost CZTS-type photovoltaic cells fully deposited by Spray Pyrolysis</i> .....	27
S. Hosokawa, Y. Ideguchi, K. Kamimura, N. Happo, K. Kimura, K. Hayashi, Y. Ebusu, T. Ozaki, Y. Yoda, H. Ishii, M. Kitaura, M. Sasak <i>An x-ray fluorescence holographic study on a <math>Bi_2Te_3:Mn</math> topological insulator</i> .....	28
O. Iaseniuc, M. Iovu, O. Bordian <i>Steady-state and transient photoconductivity of some ternary amorphous thin films</i> .....	28

O. V. Iaseniuc, M. S. Iovu, D. Dinescu, M. Enachescu <i>Optical spectroscopy of <math>(As_4S_3Se_3)_{1-x}Sn_x</math> and <math>Ge_xAs_xSe_{1-2x}</math> chalcogenides</i> .....	29
Y. Ideguchi, J. R. Stellhorn, S. Hosokawa, N. Happo, K. Kimura, K. Hayashi, H. Okazaki, A. Yamashita, Y. Takano <i>X-ray fluorescence holographic study on high-temperature superconductor <math>FeSe_{0.4}Te_{0.6}</math></i> .....	30
L. Isac, A. Duta <i>Copper sulfides as materials with promising potential in dyes photodegradation</i> .....	30
B. D. Klee, J. R. Stellhorn, S. Hosokawa, M. Krbal, N. Boudet, N. Blanc, W.-C. Pilgrim <i>Structure determination of amorphous <math>(Ga_2Se_3)_{25}(GeSe_2)_{75}</math> by anomalous X-ray scattering</i> .....	31
P. Kostka, M. Iezid, O.Bošák, R. Yatskiv, J. Zavadil, N. Bašinová, M. Legouera, M. Kubliha, D. Le Coq <i>Optical and electrical properties of <math>Sb_2O_3</math>-<math>ZnBr_2</math> oxybromide glasses</i> .....	32
O. Kondrat, R. Holomb, A. Csik, V. Takáts, M. Veres, N. Tsud, M Vondráček, V. M. Mitsa <i>In situ versus ex situ investigations of the <math>As_2S_3</math> nanolayers modified by near bandgap laser treatment</i> .....	32
Amera Z. Mahmoud <i>Effect of composition and thermal annealing on the electrical conduction of <math>Se_{85-x}Te_{15}Sb_x</math> glasses</i> .....	33
V.S. Minaev, S.P. Timoshenkov, S.N. Novikov, N.E. Korobova, V.V. Kalugin <i>Genesis of nanoheteromorphous glassforming melt and process of glass transition</i> .....	34
V. Mitsa, A. Feher, S. Petretskij, R. Holomb, V. Tkac <i>Hysteresis of low temperature thermal conductivity, Boson peak in glassy (g) <math>As_2S_3</math> and low frequency ring and branched <math>As_nS_m</math> clusters vibrations</i> .....	34
S. Molnar, V. Takacs, R. Bohdan, S. Misak, I. Csarnovics, Y. Kaganovsky, S. Kökényesi <i>Investigations of phase-modulated optical recording in amorphous chalcogenide layers from As-Se-Te system</i> .....	35
M. Reinfelde, Z. Ivanova, M. Mitkova, T. Nichol, J. Teteris <i>Photoinduced mass transport in Ge-Se amorphous films</i> .....	36
S. A. Sergheev, O. V. Iaseniuc, M. S. Iovu <i>Electron-beam recording of diffractive gratings in <math>(As_4S_3Se_3)_{1-x}Sn_x</math> amorphous thin films</i> .....	36
O. Shylenko, V. Bilanych, A. Feher, V. Rizak, V. Komanicky <i>Comparison of sensitivity of <math>Ge_9As_9Se_{82}</math> and <math>Ge_{16}As_{24}Se_{60}</math> thin films to irradiation with electron beam</i> .....	37
F. Skuban, S. R. Lukić-Petrović, M. V. Šiljegović, D. M. Petrović, M. Slankamenac <i>Study of dielectric properties of some bulk Cu-As-Se-I chalcogenides</i> .....	38
I. Studenyak, V. Izai, A. Bendak, P. Kúš, S. Kökényesi <i>High-conductive <math>Cu_6PS_5I</math>-based thin films: structural, electrical and optical properties</i> .....	38
V. J. Sukyte, L. Samardokas, R. Ivanauskas, A. Ivanauskas, I. Ancutiene <i>Review of physical-chemical properties and applications of chalcopolythionic acids</i> .....	39
N. Tanwar, V. K. Saraswat <i>Study the entropy change in glassy region under non-isothermal conditions for <math>Ge_{25-x}Se_{75}Sb_x</math> (<math>x = 12, 15</math> and <math>18</math>) chalcogenide glasses</i> .....	40

A. Velea, G. Socol, C. Mihai, A. Lőrinczi, I. D. Simandan, G. Schinteie, F. Sava <i>Thermal stability of heterojunction interfaces in GaSb/GeTe, GaSb/SnSe and SnSe/GeTe bilayers</i> .....	40
I. M. Wanjiku <i>Crystallization kinetics of In-Se chalcogenide glasses for phase change memory (PRAM) applications</i> .....	41
<i>Author Index</i> .....	43

However, the uses of standard fitting models which are presented into ellipsometre data base give not sufficient accuracy. Individual fitting model based on the well-established exponential absorption inside the band gap tail and Tauc fundamental absorption was developed.

### Dynamic Taylor cone formation on chalcogenide films surface

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We investigated the formation of surface reliefs during the interaction of an electron beam (EB) with  $\text{Ge}_9\text{As}_9\text{Se}_{82}$  films. The films (thicknesses  $2\mu\text{m}$ ) were irradiated by an EB using a scanning electron microscope (Tescan, model VEGA) in dose range  $G=9.3\times 10^3\text{--}9.3\times 10^7\ \mu\text{C}/\text{cm}^2$ . A square lattice of dots was exposed on the surface of films. Surface relief of the film was studied by atomic force microscope (Bruker, model ICON). It has been detected that three distinct types of surface features are formed in that dose range. In dose interval  $9.3\times 10^3\text{--}2.8\times 10^5\ \mu\text{C}/\text{cm}^2$  the EB induces the formation of cones with a Gaussian profile. The cone height is  $250\text{--}270\ \text{nm}$ . In dose interval  $5.6\times 10^5\text{--}1.9\times 10^6\ \mu\text{C}/\text{cm}^2$  the cone surface protrudes upward along the surface normal and becomes sharper, eventually evolving into a Taylor cone. With increasing exposure dose its height increases from  $380\ \text{nm}$  to  $560\ \text{nm}$ . In dose interval  $4.6\times 10^6\text{--}9.3\times 10^7\ \mu\text{C}/\text{cm}^2$  a combined shape relief is formed. We observe the formation of a crater with depth  $530\ \text{nm}$  and a giant Taylor cone ( $750\text{--}2510\ \text{nm}$ ) on the edge of each crater. The formation of the surface relief is caused by structural changes in the film and the emergence of the space charge region (SCR) during the interaction between  $\text{Ge}_9\text{As}_9\text{Se}_{82}$  film and EB. We find that several distinct types of surface features can be formed, depending on density and size of deposited charge into SCR. Taylor cones formed during electrohydrodynamic material flow, which occurs in SCR when certain instability limits are met. We find that development of electrohydrodynamic instability on the film surface occurs when the pressure forces of the electric field into space charge region exceed the pressure of surface tension forces. We believe that observed phenomena are interesting not only from fundamental but also applications perspective.

### Influence of size factors on the formation of surface relief in amorphous chalcogenide films during periodic charge deposition by electronic beam

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Changes in shape and parameters of electron beam (EB) induced surface relief of chalcogenide films have been investigated depending on the film thickness and distance between the irradiated areas. For measurements we used  $\text{Ge}_9\text{As}_9\text{Se}_{82}$  film with thicknesses  $3.0\mu\text{m}$ ,  $3.5\mu\text{m}$ ,  $4.5\mu\text{m}$  on sapphire substrates. We found that the film thickness, the distance between irradiated areas and charge removal rate affects characteristics of surface relief formation in the high dose regime. Significant change in surface relief is observed in the dose interval  $4.6\times 10^6\text{--}9.3\times 10^7\ \mu\text{C}/\text{cm}^2$  when distance between irradiated areas less than  $6\mu\text{m}$  decreases. At dose  $9.3\times 10^7\ \mu\text{C}/\text{cm}^2$  this relief consists from craters with two different depths ( $250\text{nm}$ ,  $800\text{nm}$ ) and giant ( $2.5\mu\text{m}$ ) spires formed at the edge of the big crater. Shallow and large craters appear in alternating

manner in chessboard-like arrangement. Our result is explained by the formation of charge distribution bilayer under electron irradiation of chalcogenide films and subsequent flow of the self-consistent currents generated in irradiated area. The size of the interaction region of the EB with  $\text{Ge}_9\text{As}_9\text{Se}_{82}$  film has been determined ( $6.2\mu\text{m}$ ). The appearance of surface relief is associated with formation into film the space charge region (SCR) induced by EB. We find that when matrix period is of comparable with size SCR the chessboard-like lattice is formed in films with thickness larger than  $3\mu\text{m}$  by the overlap of neighboring space charge regions in irradiated areas. When matrix period is larger than SCR surface reliefs generated in single step charge deposition step are identical. When film thicknesses is  $4.5\mu\text{m}$  and matrix period is  $10\mu\text{m}$  parameters of electron-induced relief reach gigantic values: cone height -  $3880\text{nm}$ , depth of crater -  $1310\text{nm}$ . We demonstrate that by variation of lattice period during periodic charge deposition in chalcogenide thin films we could directly experimentally define SCR size in these materials.

### Relaxation processes in chalcogenide glasses

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Relaxation processes in chalcogenide glasses of the Se, As-Se, Ge-As-Se systems have been investigated by dynamic mechanical analysis technique. Temperature dependence of internal friction and real and imaginary parts of the shear modulus of chalcogenide glasses were measured in the mode of forced torsional and bending vibrations. In selenium-rich glasses of As-Se and Ge-As-Se systems was found maxima of internal friction and of shear modulus imaginary part in the temperature range 200K-250K. This relaxation process can be identified as  $\beta$ -process of mechanical relaxation. Its activation energy lie in the range of 0.5-1 eV. Parameter relaxation time distribution was determined from the cole-cole diagram (0.15-0.2). We shown that the cause of  $\beta$ -process of these glasses can be relaxation of their structure in region of local disordering in the vicinity of selenium atoms with dangling bonds, as well as the fluctuation microcavities. The relaxation maximum of internal friction is observed in the glass transition temperature for all glasses under investigation. This relaxation process was classified as  $\alpha$ -process of mechanical relaxation these glasses. This process is caused by complete defreezing of the mobility of glass structural elements. Highelasticity plateau is observed on the temperature dependence of the shear modulus in Se-rich glasses of Ge-As-Se system as well as in Se and in glasses As-Se systems. Parameter relaxation time distribution was determined from the Cole-Cole diagrams. It was found that the full relaxation spectrum of chalcogenide glasses formed three relaxation processes:  $\alpha$ -relaxation is determined by full unfreezing of mobility of the structure units and the transition of glasses into the heighelastic state;  $\beta$ -relaxation which can be associated with the relaxation of glass structure in regions of local disordering in the vicinity of atoms with unsaturated (dangling) bonds;  $\gamma$ -relaxation of selenium is determined by the twolevel systems in the atomic twohole potential.

### Ultrasound modulation of the structure of glassy chalcogenides

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Our previous experiments on ultrasonic treatment of the softening Se-X glasses (X= Te, S, As, Cl) [1-4] are reconsidered here using a special representation of the optical transmission data for the Se-Te series as an example. The obtained results lead to the conclusion that glass behaves as the *self-organizing* system of the dissipative type. A characteristic dissipative pattern is considered as the *bond wave* [5], whose wavefronts